Amendments to the Specification

~~A semiconductor component comprising a semiconductor chip 2 made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization 7 in a contact window, and said inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection 9, characterized in that the inner connection metallization comprises a reinforcing system 8 having an open grid structure on the doped silicon substrate.~~

~~Fig. 1~~

Consistent with an example embodiment, there is a semiconductor component comprising a semiconductor chip made of a doped silicon substrate. The chip is doped into a semiconductor device and structured, and includes an inner connection metallization in a contact window. The inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection, wherein the inner connection metallization comprises a reinforcing system having an open grid structure on the doped silicon substrate.